IRFPF30

Vishay Siliconix



TO-247AC

PRODUCT SUMMARY

V_{DS} (V)

R_{DS(on)} (Ω)

Q_{qs} (nC)

Q_{ad} (nC)

Q_a (max.) (nC)

Configuration

Power MOSFET

D

N-Channel MOSFET

3.7

900

78

10

42

Single

V_{GS} = 10 V

FEATURES

- Dynamic dV/dt rated
- Repetitive avalanche rated
- · Isolated central mounting hole
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

Note

^t This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247AC package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because its isolated mounting hole. It also provides greater creepage distances between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free	IRFPF30PbF

ABSOLUTE MAXIMUM RATINGS (T _C	= 25 °C, unless otherwi	se noted)		
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	900	- V
Gate-source voltage		V _{GS}	± 20	v
Continuous drain current	V_{GS} at 10 V $T_C = 25 \degree C$	1_	3.6	
Continuous drain current	$T_{\rm C} = 100 ^{\circ}{\rm C}$		2.3	А
Pulsed drain current ^a		I _{DM}	14	
Linear derating factor			1.0	W/°C
Single pulse avalanche energy ^b		E _{AS}	170	mJ
Repetitive avalanche current ^a		I _{AR}	3.6	A
Repetitive avalanche energy ^a		E _{AR}	13	mJ
Maximum power dissipation	T _C = 25 °C	PD	125	W
Peak diode recovery dV/dt ^c		dV/dt	1.5	V/ns
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) for 10 s			300 ^d	
Mounting torque	6-32 or M3 screw		10	lbf ∙ in
Mounting torque	0-52 OF IVIS SCIEW	ĺ	1.1	N · m

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. V_{DD} = 50 V, starting T_J = 25 °C, L = 24 mH, R_g = 25 Ω , I_{AS} = 3.6 A (see fig. 12)

c. $I_{SD} \le 3.6$ A, dI/dt ≤ 70 A/µs, $V_{DD} \le 600$, $T_J \le 150$ °C

S22-0057-Rev. C, 31-Jan-2022

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THERMAL RESISTANCE RAT	INGS			
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R _{thJA}	-	40	
Case-to-sink, flat, greased surface	R _{thCS}	0.24	-	°C/W
Maximum junction-to-case (drain)	R _{thJC}	-	1.0	

PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						•	
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_D = 2$	50 µA	900	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	Reference to 25	$^{\circ}$ C, I _D = 1 mA	-	1.1	-	V/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 2$	250 μΑ	2.0	-	4.0	V
Gate-source leakage	I _{GSS}	$V_{GS} = \pm 20 V$		-	-	± 100	nA
Zero gate voltage drain current	lana	V _{DS} = 900 V, V _{GS}	_S = 0 V	-	-	100	μA
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 720 V, V_{GS}$	_S = 0 V, T _J = 125 °C	-	-	500	μΛ
Drain-source on-state resistance	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 2.2 A ^b	-	-	3.7	Ω
Forward transconductance	g _{fs}	$V_{DS} = 100 \text{ V}, \text{ I}_{D} =$	= 2.2 A ^b	2.3	-	-	S
Dynamic							
Input capacitance	C _{iss}	$V_{GS} = 0 V,$		-	1200	-	
Output capacitance	C _{oss}	$V_{DS} = 25 V,$		-	320	-	pF
Reverse transfer capacitance	C _{rss}	f = 1.0 MHz, see	e fig. 5	-	200	-	
Total gate charge	Qg			-	-	78	
Gate-source charge	Q _{gs}	V _{GS} = 10 V	$I_D = 3.6 \text{ A}, V_{DS} = 360 \text{ V}$ see fig. 6 and 13 ^b	-	-	10	nC
Gate-drain charge	Q _{gd}		see lig. o and to	-	-	42	
Turn-on delay time	t _{d(on)}			-	14	-	
Rise time	t _r	V _{DD} = 450 V, I _D =	= 3.6 A,	-	25	-	
Turn-off delay time	t _{d(off)}	$R_g = 12 \Omega, R_D =$	$R_g = 12 \Omega$, $R_D = 120 \Omega$, see fig. 10 ^b		90	-	ns
Fall time	t _f			-	30	-	
Internal drain inductance	L _D	Between lead,	- d	-	5.0	-	
Internal source inductance	L _S	6 mm (0.25") from package and cent die contact		-	13	-	nH
Drain-Source Body Diode Characteristic	s						
Continuous source-drain diode current	I _S	MOSFET symbo		-	-	3.6	
Pulsed diode forward current ^a	I _{SM}	showing the integral reverse p - n junction did	ode	-	-	14	A
Body diode voltage	V _{SD}	$T_{\rm J} = 25 \ ^{\circ}{\rm C}, \ I_{\rm S} = 3$	3.6 A, V _{GS} = 0 V ^b	-	-	1.8	V
Body diode reverse recovery time	t _{rr}		3.6 A, dl/dt = 100 A/µs ^b	-	430	650	ns
Body diode reverse recovery charge	Q _{rr}	$I_{\rm J} = 25^{-1} {\rm G}, I_{\rm F} = 3$	$5.0 \text{ A}, \text{ u/ul} = 100 \text{ A/}\mu\text{S}^{10}$	-	1.4	2.1	μC
Forward turn-on time	t _{on}	Intrinsic turn-on	time is negligible (turn-on	is domin	ated by L	s and Ln)	

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width \leq 300 µs; duty cycle \leq 2 %.

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

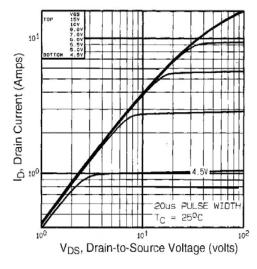


Fig. 1 - Typical Output Characteristics, $T_C = 25 \ ^{\circ}C$

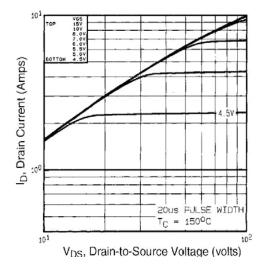


Fig. 2 - Typical Output Characteristics, $T_C = 150$ °C

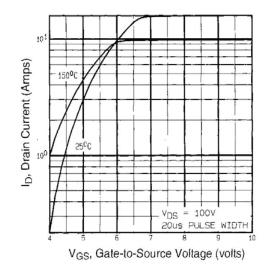


Fig. 3 - Typical Transfer Characteristics

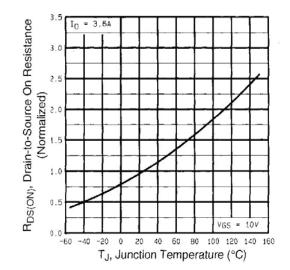


Fig. 4 - Normalized On-Resistance vs. Temperature





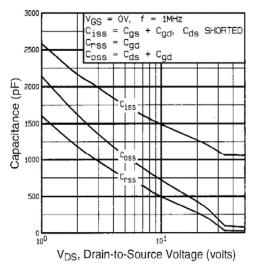


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

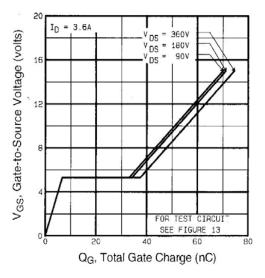


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

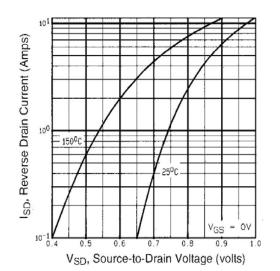


Fig. 7 - Typical Source-Drain Diode Forward Voltage

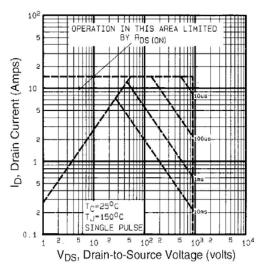


Fig. 8 - Maximum Safe Operating Area



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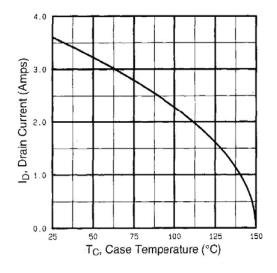


Fig. 9 - Maximum Drain Current vs. Case Temperature

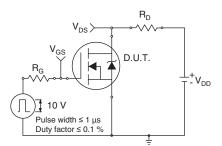


Fig. 10 - Switching Time Test Circuit

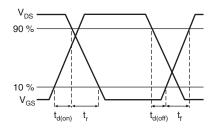


Fig. 11 - Switching Time Waveforms

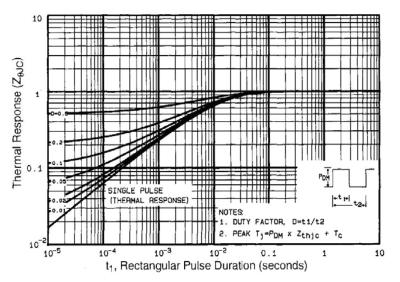


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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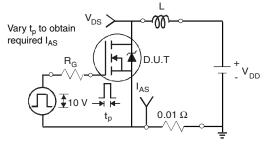


Fig. 13 - Unclamped Inductive Test Circuit

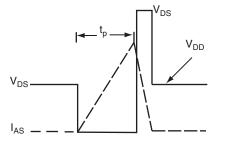


Fig. 14 - Unclamped Inductive Waveforms

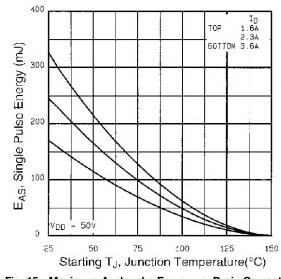


Fig. 15 - Maximum Avalanche Energy vs. Drain Current

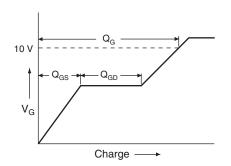
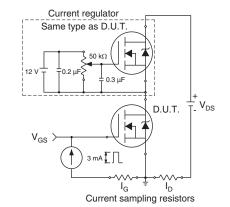


Fig. 16 - Basic Gate Charge Waveform





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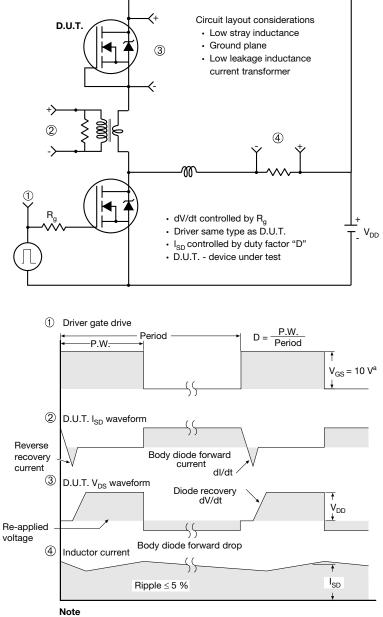
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Peak Diode Recovery dV/dt Test Circuit



a. V_{GS} = 5 V for logic level devices

Fig. 18 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91249.



TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9





Section C--C, D--D, E--E

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
А	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØP	3.56	3.65	7
Ø P1	7.19	7.19 ref.	
Q	5.31	5.69	
S	5.54	5.74	

Notes

- ⁽¹⁾ Package reference: JEDEC[®] TO247, variation AC
- (2) All dimensions are in mm
- ⁽³⁾ Slot required, notch may be rounded
- ⁽⁴⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁵⁾ Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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VERSION 2: FACILITY CODE = Y



	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
А	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
с	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØΡ	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

Notes

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- ⁽²⁾ Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- ⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- ⁽⁷⁾ Outline conforms to JEDEC outline TO-247 with exception of dimension c



VERSION 3: FACILITY CODE = N



	MILLIN	IETERS		MILLIN	IETERS
DIM.	MIN.	MAX.	DIM.	MIN.	MAX.
А	4.65	5.31	D2	0.51	1.35
A1	2.21	2.59	E	15.29	15.87
A2	1.17	1.37	E1	13.46	-
b	0.99	1.40	е	5.46	BSC
b1	0.99	1.35	k	0.:	254
b2	1.65	2.39	L	14.20	16.10
b3	1.65	2.34	L1	3.71	4.29
b4	2.59	3.43	N	7.62	BSC
b5	2.59	3.38	Р	3.56	3.66
С	0.38	0.89	P1	-	7.39
c1	0.38	0.84	Q	5.31	5.69
D	19.71	20.70	R	4.52	5.49
D1	13.08	-	S	5.51	BSC

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

⁽²⁾ Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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